

## ABSTRACT

The present invention relates to a method for preparing manganese-based nitride having nearly zero temperature coefficient of resistivity and more particularly, to the effective method for preparing manganese-based nitride expressed by the formula (1), wherein the manganese-based nitride, prepared by heating the stoichiometric mixture of  $Mn_2N$  and Cu in an evacuated quartz tube, provides some advantages in that i) the use of the  $Mn_2N$  compound as a reactant, the formation of impurities and nitrogen evaporation may be prevented, and ii) through nitrogen is tightly bonded between metals, the manganese-based nitride has extremely low (46 ppm/K) temperature coefficient of resistivity.

